METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, SUBSTRATE PROCESSING APPARATUS, AND PROGRAM

ABSTRACT

There is provided a technique that includes a first act of modifying a film containing a silazane bond by heating a substrate, in which the film containing the silazane bond is formed over a surface of the substrate, to a first temperature and by supplying a first processing gas containing hydrogen peroxide to the substrate; and after the first act, a second act of modifying the film containing the silazane bond by heating the substrate to a second temperature higher than the first temperature and by supplying a second processing gas containing hydrogen peroxide to the substrate.

Figure 4